

Development of Nonfullerene Acceptors with Spiro-substituted Fluorene Units

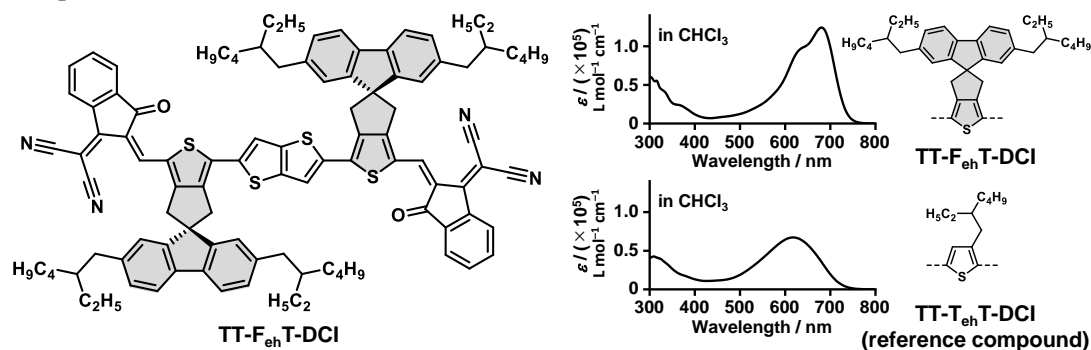
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As the candidate of acceptor materials in organic photovoltaics (OPVs), considerable efforts have been devoted to developing new electron-accepting π -conjugated molecules. Most of high-performance nonfullerene acceptors possess planar fused structures with bulky substituents on the central part. We have reported a series of oligothiophenes having orthogonally fused fluorene units for insulated molecular wires.¹⁻³⁾ In this molecule, the presence of cyclopentene-annellation is important to achieve planar π -conjugated backbone, and orthogonally fused fluorene unit can suppress the intermolecular interactions. In this study, to utilize the advantages of this unit, we developed new nonfullerene acceptor (**TT-F_{eh}T-DCI**).

The physical properties of **TT-F_{eh}T-DCI** were investigated by electrochemical and photophysical measurements. Cyclic voltammetry measurements showed a reduction wave with the half-wave reduction potential ($E_{\text{red}}^{1/2}$) of -0.95 V vs. Fc/Fc^+ . Based on $E_{\text{red}}^{1/2}$, the lowest unoccupied molecular orbital (LUMO) energy level of **TT-F_{eh}T-DCI** was estimated to be -3.85 eV. On UV-vis absorption measurements, **TT-F_{eh}T-DCI** showed narrower absorption bands at around 600-720 nm with higher molar extinction coefficient, compared to that of the reference compound (**TT-T_{eh}T-DCI**). This phenomenon indicates that the planarity of π -conjugated backbone was improved by the introduction of cyclopentene-annellation. From the absorption edge of 735 nm (1.69 eV) and the LUMO energy level, the highest occupied molecular orbital (HOMO) energy level was determined to be -5.54 eV.

The photovoltaic characteristics of **TT-F_{eh}T-DCI** were investigated in OPVs with an inverted configuration of [ITO/ZnO/PBDB-T (CAS No. 1415929-80-4): **TT-F_{eh}T-DCI** / MoO_x /Ag]. **TT-F_{eh}T-DCI** showed higher power conversion efficiency (PCE) than reference compound, and the maximum PCE value of 6.12% was observed.



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